

August 2006

# **FMPA2151**

# 2.4–2.5GHz and 4.9–5.9GHz Dual Band Linear Power Amplifier Module

#### **Features**

- Dual band operation in a single package design
- Integrated bias bypass
- >33dB modulated gain 2.4 to 2.5GHz band
- >33dB modulated gain 4.9 to 5.9GHz band
- 3.0% EVM at 19dBm modulated power out (2.4GHz)
- 3.5% EVM at 19dBm modulated power out (5.5GHz)
- 3.3V positive supply operation
- Separate integrated power detectors with 20dB dynamic range
- 16 pin 4 x 4 x 1.4mm leadless package
- Internally matched to 50Ω and DC blocked RF input/output
- Optimized for use in 802.11a/b/g applications

### **General Description**

The FMPA2151 is a dual frequency band power amplifier module designed for high performance WLAN applications in the 2.4 to 2.5GHz and the 4.90 to 5.9GHz frequency bands. The 16 pin 4 x 4 x 1.4 mm package with internal matching on both input and output to  $50\Omega$  minimizes next level PCB space and allows for simplified integration. Only two external bias bypass capacitors are required. The two on-chip detectors provide power sensing capability. The PA's low power consumption and excellent linearity are achieved using our InGaP Heterojunction Bipolar Transistor (HBT) technology.

Complimentary pin out available with part number FMPA2153 for MIMO applications.

## **Device (4 x 4 x 1.4mm)**



# **Electrical Characteristics**<sup>(1)</sup> 802.11g (2.4-2.5 GHz) OFDM Modulation (with 176 μs burst time, 100 μs idle time) 54 Mbps Data Rate, 16.7 MHz Bandwidth

| Parameter                                    | Min.  | Тур. | Max. | Units |
|--|-------|------|------|-------|
| Frequency                                    | 2.4   |      | 2.5  | GHz   |
| Collector Supply Voltage                     | 3.0   | 3.3  | 3.6  | V     |
| Mirror Supply Voltage (PA ON 2.4)            | 2.6   | 3.0  | 3.6  | V     |
| Mirror Supply Current (PA ON 2.4)            | EN S  | 0.1  |      | mA    |
| Gain   | and a | 31   |      | dB    |
| Average Packet Current @ +19dBm Pout         | Com   | 140  |      | mA    |
| EVM @ +19dBm Pout <sup>(2)</sup>             |       | 3.0  |      | %     |
| Detector Output @ +19dBm Pout                |       | 600  |      | mV    |
| Detector Output @ +7dBm Pout                 |       | 280  |      | mV    |
| POUT Spectral Mask Compliance <sup>(3)</sup> |       | +20  |      | dBm   |

#### Notes:

1.  $V_{CC}$  = 3.3V, PA ON 2.4 = 3.3V,  $T_A$  = 25°C, PA is constantly biased, 50 $\Omega$  system.

Percentage includes system noise floor of EVM = 0.8%.

Measured at PIN at which Spectral Mask Compliance is satisfied. Two-sample windowing length applied.

# Electrical Characteristics(1) 802.11a OFDM Modulation

(with 176 µs burst time, 100 µs idle time) 54 Mbps Data Rate, 16.7 MHz Bandwidth

| Parameter  | Min. | Тур. | Max. | Units |
|--|------|------|------|-------|
| Frequency  | 4.9  |      | 5.9  | GHz   |
| Collector Supply Voltage                         | 3.0  | 3.3  | 3.6  | V     |
| Mirror Supply Voltage (PA ON 5.5)                | 2.6  | 3.0  | 3.6  | V     |
| Mirror Supply Current (PA ON 5.5)                |      | 0.1  |      | mA    |
| Gain   |      | 33   |      | dB    |
| Average Packet Current @ +19dBm Pout             |      | 240  |      | mA    |
| EVM @ +19dBm Pout <sup>(2)</sup> (4.9 to 5.9GHz) |      | 3.5  |      | %     |
| Detector Output @ +19dBm Pout                    |      | 600  |      | mV    |
| Detector Output @ +7dBm Pout                     |      | 375  |      | mV    |
| POUT Spectral Mask Compliance <sup>(3)</sup>     |      | +20  |      | dBm   |

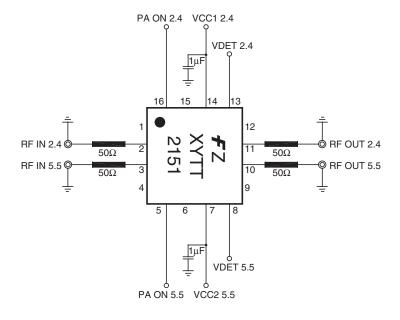
# Absolute Maximum Ratings(4)

| Symbol          | Parameter                  | Ratings     | Units |
|-----------------|----------------------------|-------------|-------|
| V <sub>CC</sub> | Positive Supply Voltage    | 6           | V     |
| Icc             | Supply Current             | 500         | mA    |
| PA ON           | Positive Bias Voltage      | 4           | V     |
| Pin             | RF Input Power             | 0           | dBm   |
| Tcase           | Case Operating Temperature | -40 to +85  | °C    |
| Tstg            | Storage Temperature        | -55 to +150 | °C    |

#### Notes:

- 1.  $V_{CC}$  = 3.3V, PA ON 5.5 = 3.3V,  $T_A$  = 25°C, PA is constantly biased,  $50\Omega$  system.
- 2. Percentage includes system noise floor of EVM = 0.8%.
- 3. Measured at PIN at which Spectral Mask Compliance is satisfied. Two-sample windowing length applied.
- 4. No permanent damage with one parameter set at extreme limit. Other parameters set to typical values.

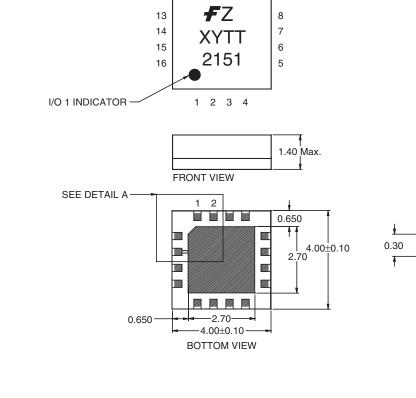
### **Schematic**

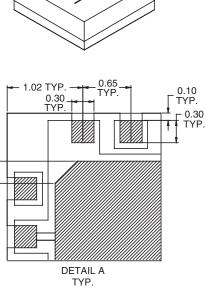


TOP VIEW 12 11 10 9

| Pin | Description |  |
|-----|-------------|--|
| 1   | GND         |  |
| 2   | RF IN 2.4   |  |
| 3   | RF IN 5.5   |  |
| 4   | GND         |  |
| 5   | PA ON 5.5   |  |
| 6   | GND         |  |
| 7   | VCC2 5.5    |  |
| 8   | VDET 5.5    |  |
| 9   | GND         |  |
| 10  | RF OUT 5.5  |  |
| 11  | RF OUT 2.4  |  |
| 12  | GND         |  |
| 13  | VDET 2.4    |  |
| 14  | VCC1 2.4    |  |
| 15  | GND         |  |
| 16  | PA ON 2.4   |  |
| 17  | CENTER GND  |  |

# **Package Outline**





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| EcoSPARK™            | IntelliMAX™         | PowerEdge™               | SuperSOT™-8            |                          |
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| Across the board.    | Around the world.™  | μSerDes™                 | TruTranslation™        |                          |
| The Power Franch     | ise <sup>®</sup>    | ScalarPump™              | UHC™                   |                          |
| Programmable Act     | ive Droop™          |                          |                        |                          |

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